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(54) Title: BLOCKING PRE-AMORPHIZATION OF A GATE ELECTRODE OF A TRANSISTOR

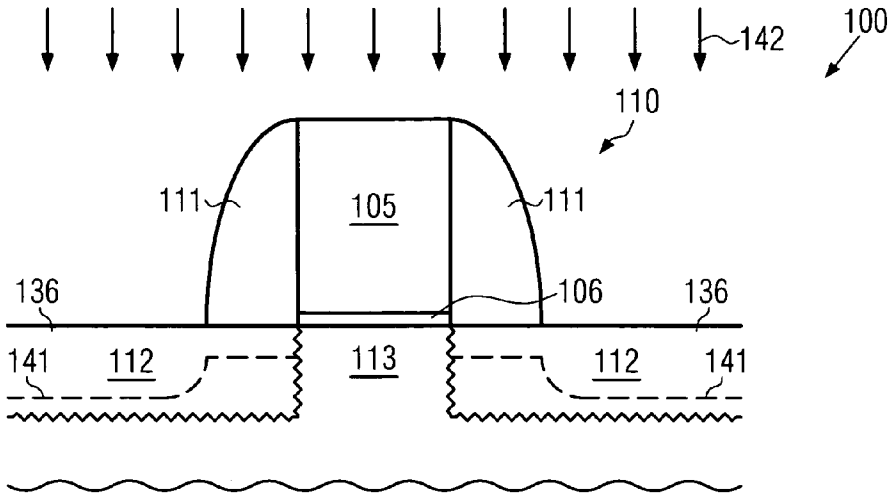


FIG. 1G

(57) Abstract: A technique is presented which provides for a selective pre-amorphization of source/drain regions of a transistor while preventing pre-amorphization of a gate electrode of the transistor. Illustrative embodiments include the formation of a pre-amorphization implant blocking material over the gate electrode. Further illustrative embodiments include inducing a strain in a channel region by use of various stressors.

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